

EH3600TTS-32.768M



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 3.3Vdc 4 Pad 3.2mm x 5.0mm Ceramic Surface Mount (SMD) 32.768MHz \pm 100ppm 0°C to +70°C

ELECTRICAL SPECIFICATIONS

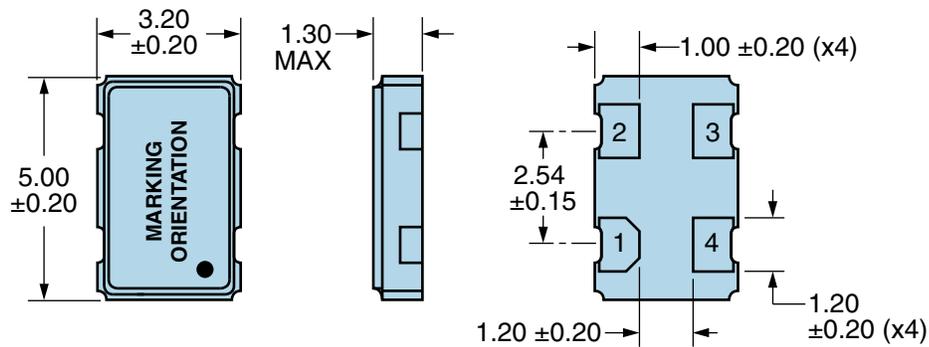
Nominal Frequency	32.768MHz
Frequency Tolerance/Stability	\pm 100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	\pm 5ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	3.3Vdc \pm 10%
Input Current	35mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.7Vdc Minimum (IOH = -8mA)
Output Voltage Logic Low (Vol)	0.5Vdc Maximum (IOL = +8mA)
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 \pm 5(%) (Measured at 50% of waveform)
Load Drive Capability	30pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	70% of Vdd Minimum to enable output, 20% of Vdd Maximum to disable output, No Connect to enable output.
Absolute Clock Jitter	\pm 250pSec Maximum, \pm 100pSec Typical
One Sigma Clock Period Jitter	\pm 50pSec Maximum, \pm 40pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)

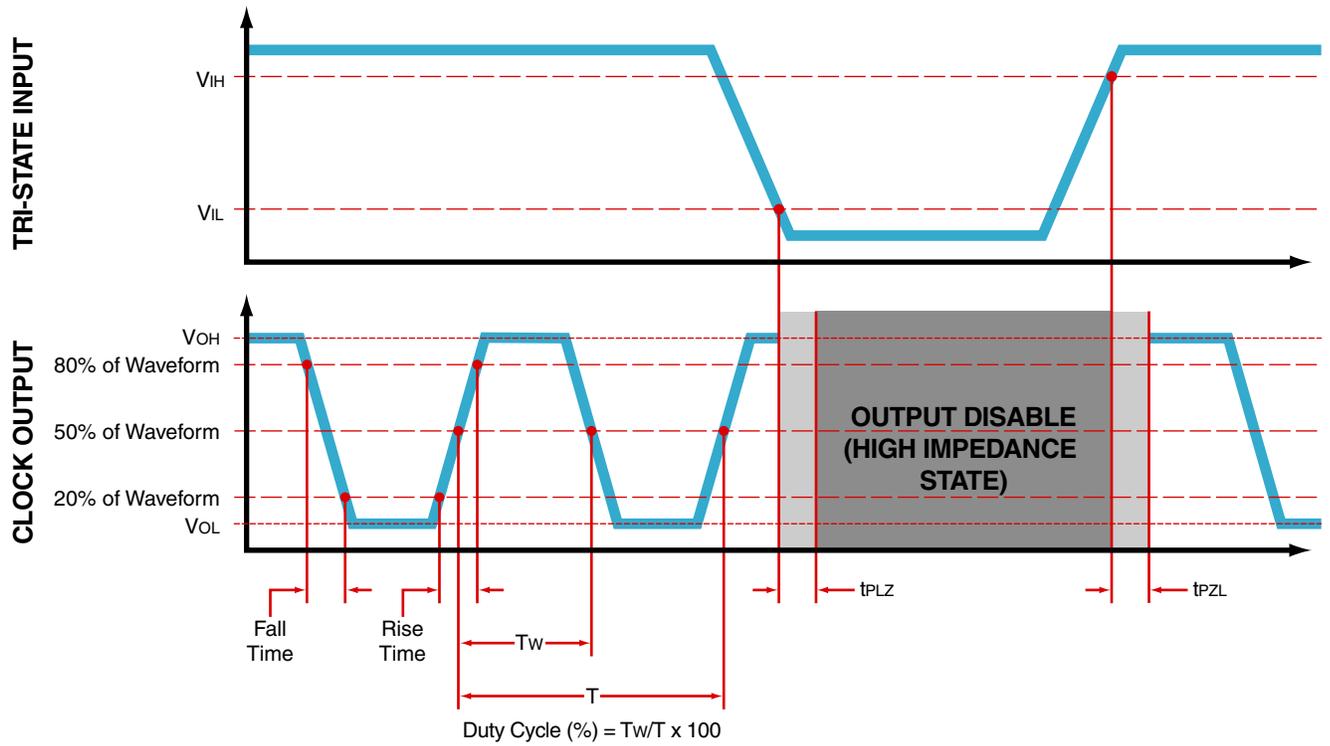


PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage

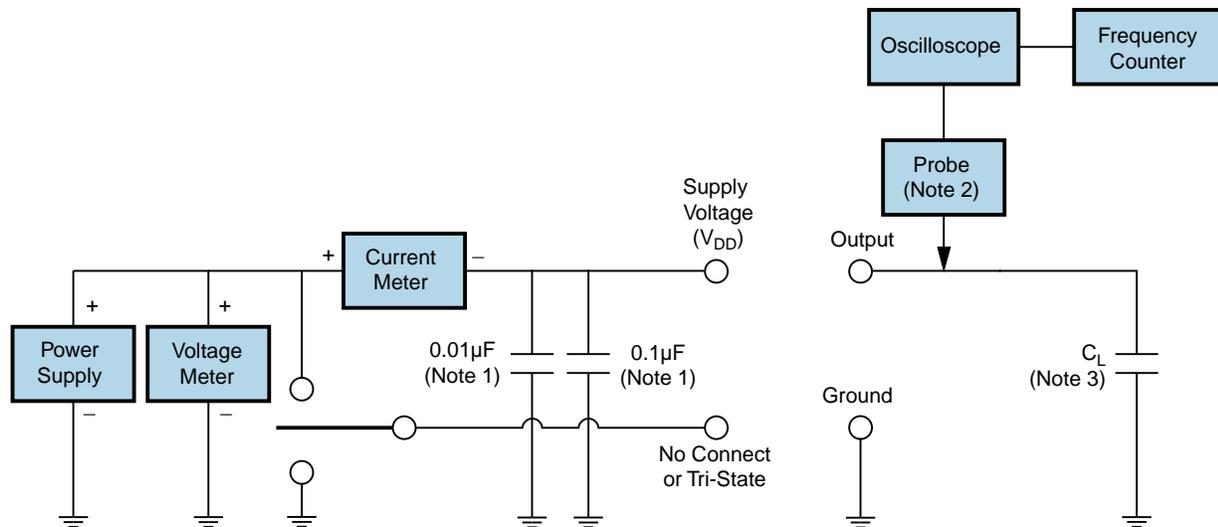
LINE	MARKING
1	E32.768 <i>E=Ecliptek Designator</i>
2	XXXXX <i>XXXXX=Ecliptek Manufacturing Identifier</i>

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OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance ($<12\text{pF}$), 10X attenuation factor, high impedance ($>10\text{Mohms}$), and high bandwidth ($>300\text{MHz}$) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.